

### **Description**

The FDV301N uses advanced trench technology to provide excellent  $R_{\text{DS(ON)}}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.



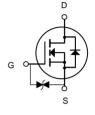
**SOT-23** 

#### **General Features**

 $V_{DS} = 30V I_{D} = 0.1A$ 

 $R_{DS(ON)}$  < 2.20@  $V_{GS}$ =10V

ESD Rating: HBM ≥ 2000V



N-Channel MOSFET

## **Application**

Battery protection

Load switch

Uninterruptible power supply

### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
FDV301N	SOT-23	HXY MOSFET	3000

### Absolute Maximum Ratings (T<sub>C</sub>=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit	
V <sub>DS</sub>	Drain-Source Voltage		30	V
Vgs	Gate-Source Voltage		±20	V
		T <sub>A</sub> =25℃	0.1	
$I_D$	Continuous Drain Current (T <sub>J</sub> =150°C)	T <sub>A</sub> =100°C	0.07	Α
Ірм	Drain Current-Pulsed (Note 1)		0.65	Α
P <sub>D</sub>	Maximum Power Dissipation		0.35	W
T <sub>J</sub> ,T <sub>STG</sub>	Operating Junction and Storage Temperature Range		-55 To 150	$^{\circ}$ C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)		200	°C/W



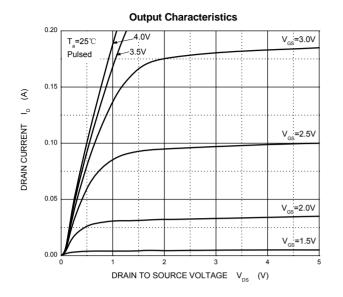
## Electrical Characteristics (T<sub>A</sub>=25°Cunless otherwise noted)

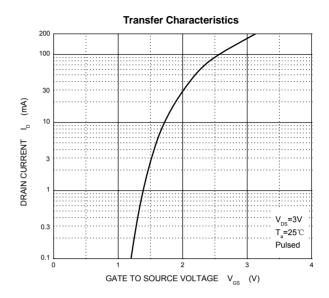
Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Off Characteristics	Characteristics					
Drain-Source Breakdown Voltage	VDS	Vgs = 0V, ID = 10µA	30			V
Zero Gate Voltage Drain Current	Idss	V <sub>DS</sub> =30V,V <sub>GS</sub> = 0V			0.2	μA
Gate –Source leakage current	Igss	V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V			±2	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> =100μA	8.0		1.5	V
Drain-Source On-Resistance	RDS(on)	V <sub>G</sub> S = 10V, I <sub>D</sub> =10mA		1.5	2.2	Ω
Dialii-Source Off-Nesistance		Vgs =4.5V,lp =1mA		2	3	Ω
Forward Transconductance	grs	V <sub>DS</sub> =3V, I <sub>D</sub> = 10mA	20			mS
Dynamic Characteristics*	Dynamic Characteristics*					
Input Capacitance	Ciss			13		pF
Output Capacitance	Coss	V <sub>DS</sub> =5V,V <sub>GS</sub> =0V,f =1MHz		9		pF
Reverse Transfer Capacitance	Crss			4		pF
Switching Characteristics*						
Turn-On Delay Time	<b>t</b> d(on)			15		ns
Rise Time	tr	Vgs =5V, Vdd =5V,		35		ns
Turn-Off Delay Time	td(off)	I <sub>D</sub> =10mA, Rg=10 $\Omega$ , R <sub>L</sub> =500 $\Omega$ ,		80		ns
Fall Time	tf			80		ns

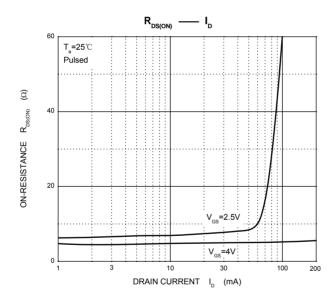
<sup>\*</sup> These parameters have no way to verify.

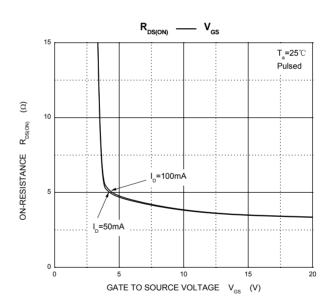


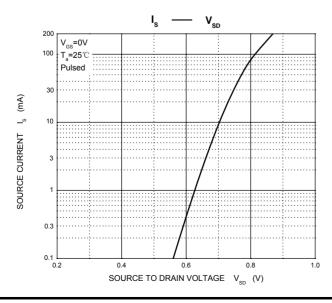
# **Typical Characteristics**

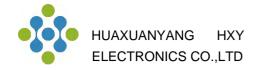




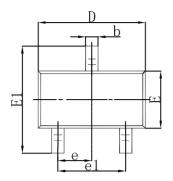


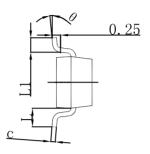


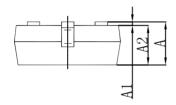




## **SOT-23 Package Outline Dimensions**

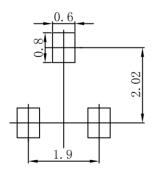






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	0 TYP 0.037 TYP		7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550	) REF	0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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